The invention relates to the information recording on photothermoplastic and electron-diffraction carriers.

The photosensitive layer for information carriers, including solid solution of sulphide and arsenic triselenide, also contains bismuth, in the following ratio, %:

As2S3	79,2…93,5;
As2Se3	5,0…20,0;
Bi	0,8…1,5.

The result of the invention consists in increasing the sensibility of the photosensitive layer of the information carrier in the ultraviolet region of the spectrum.

Claims: 1